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A cross-sectional view of a semiconductor device 10A. The device features a substrate 11A with a base layer 11B. A central region contains a stack of layers 12, 13, and 14, which is flanked by two side regions 15 and 16. The side regions 15 and 16 are separated from the central region by a gap 17A. The device is mounted on a base 18, which is supported by two pillars 19. The device is shown in a cross-section along a line X-X'.

A cross-sectional view of a semiconductor device 10A. The device features a substrate 11A with a base layer 11B. A central region contains a stack of layers 12 and 13, topped with a cap layer 14. This central region is flanked by two side regions, each containing a stack of layers 15 and 16. The side regions are connected to the central region by a bridge structure 17. The entire device is mounted on a carrier 18, which is supported by a base 19. The carrier 18 has a central opening 20 and two side openings 21. The base 19 has a central opening 22.

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FIG.3

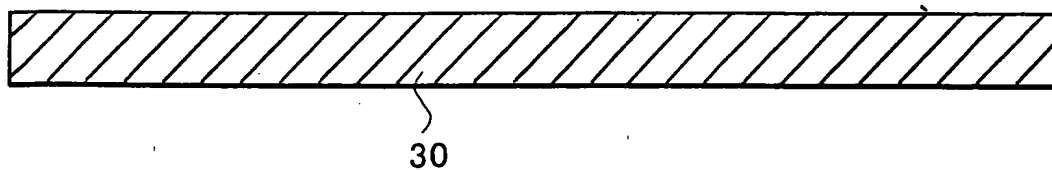


FIG.4

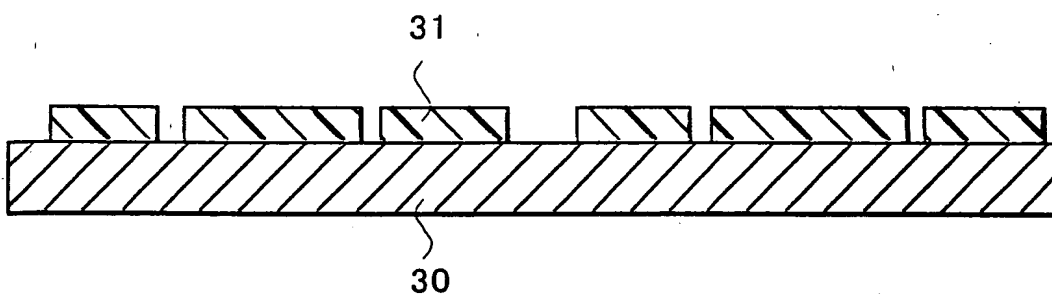


FIG.5

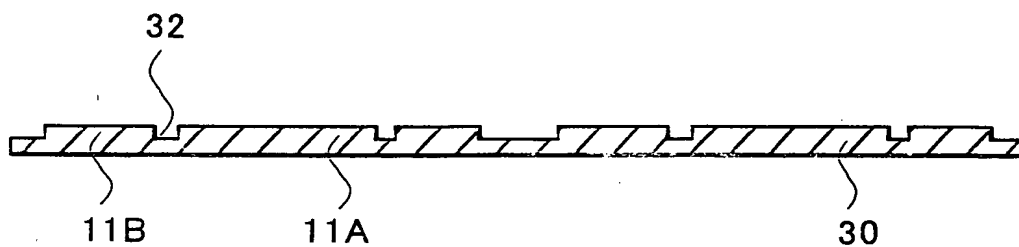
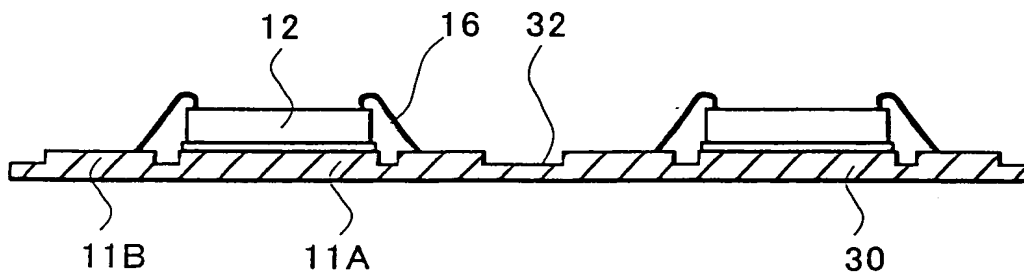


FIG.6



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FIG.7

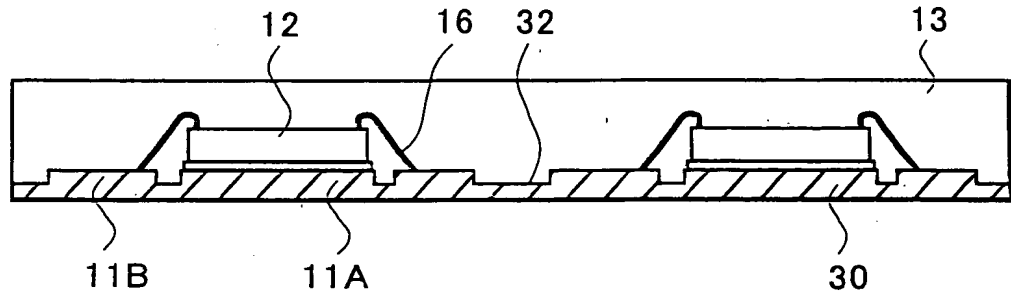


FIG.8

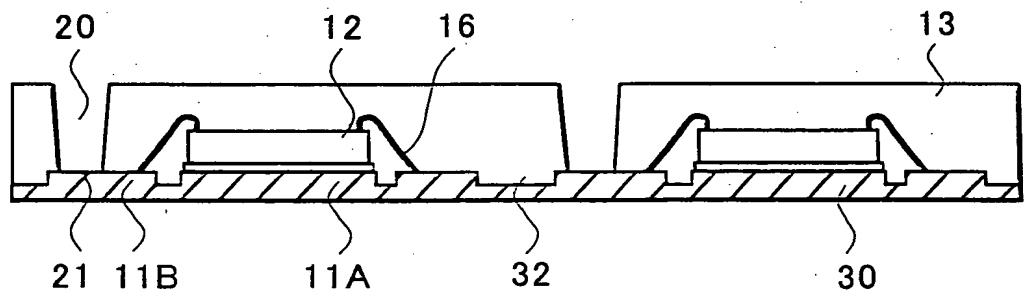
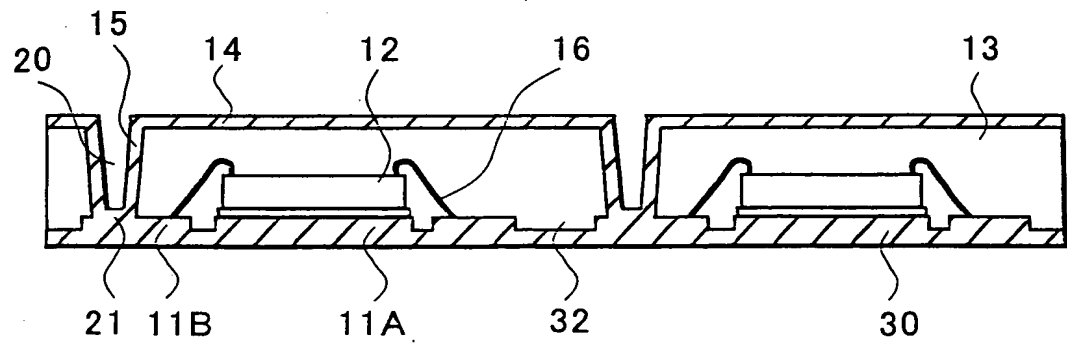


FIG.9



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FIG.10

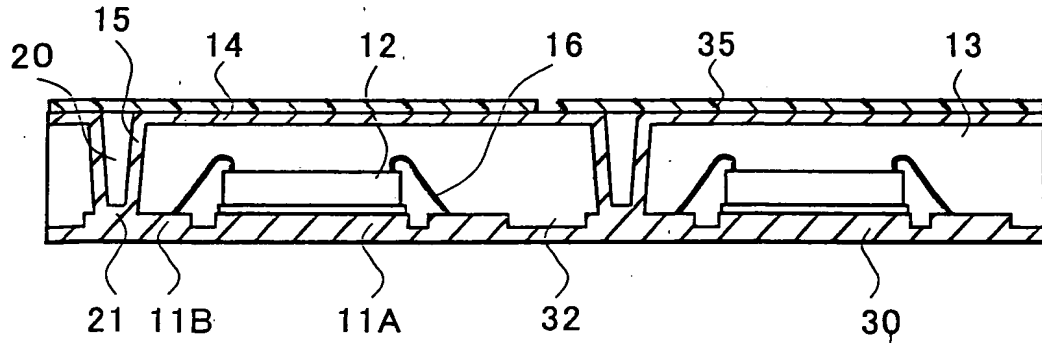


FIG.11

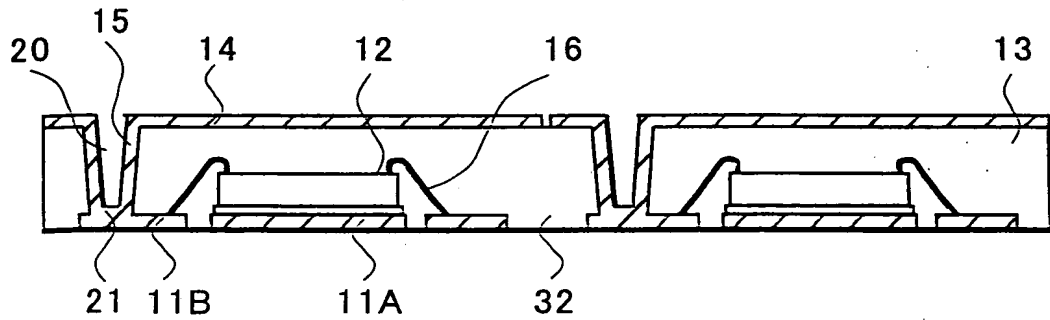
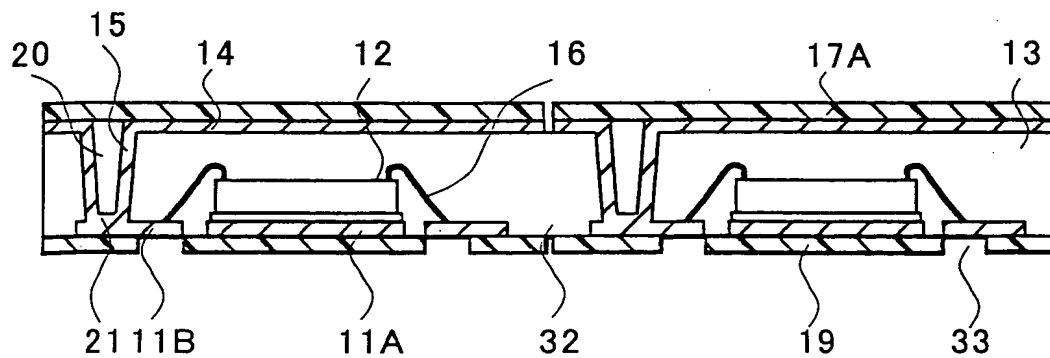


FIG.12



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FIG.13

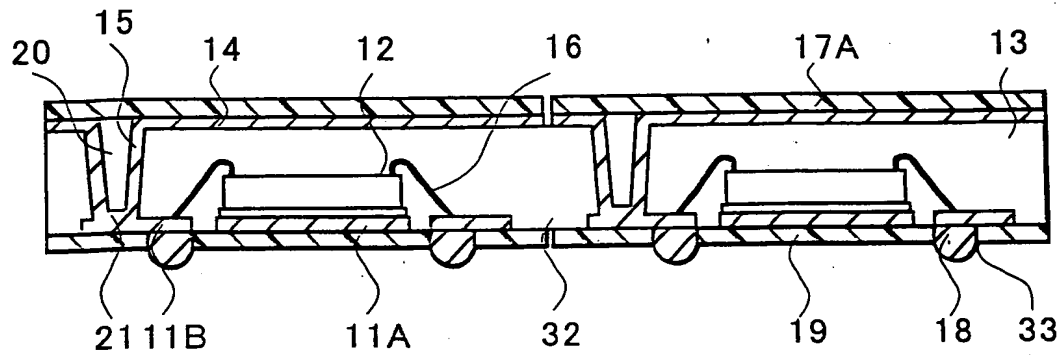
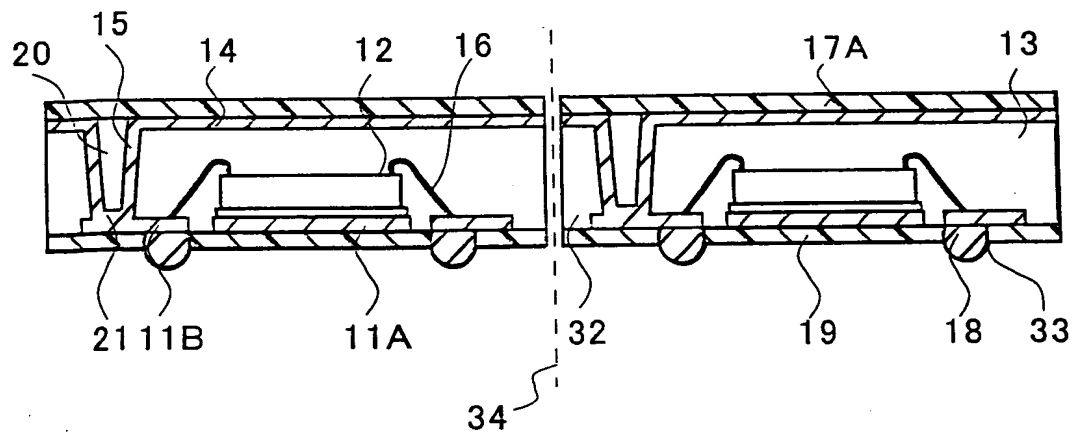


FIG.14



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FIG.15

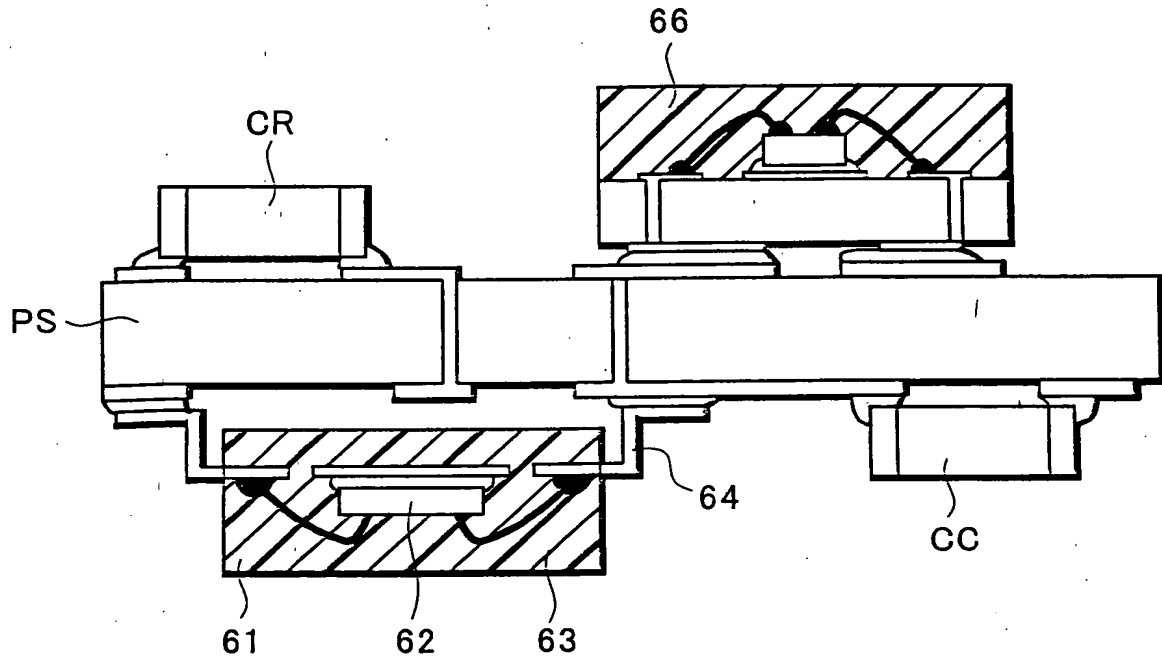


FIG.16

